

FAN8038B (KA3038)

4-Channel Motor Drive IC

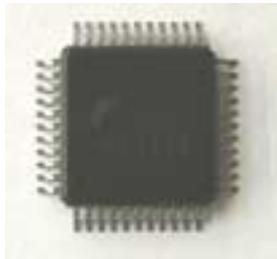
Features

- 4-CH H-bridge driver
- Built-in DC/DC converter controller circuit
- Built-in reset circuit
- Built-in battery charging circuit
- Built-in voltage drop detector
- Built-in thermal shutdown circuit
- Built-in general op-amp
- Low power consumption
- Built-in power controller circuit

Description

FAN8038B is monolithic IC for portable CD player.

44-QFP-1010B



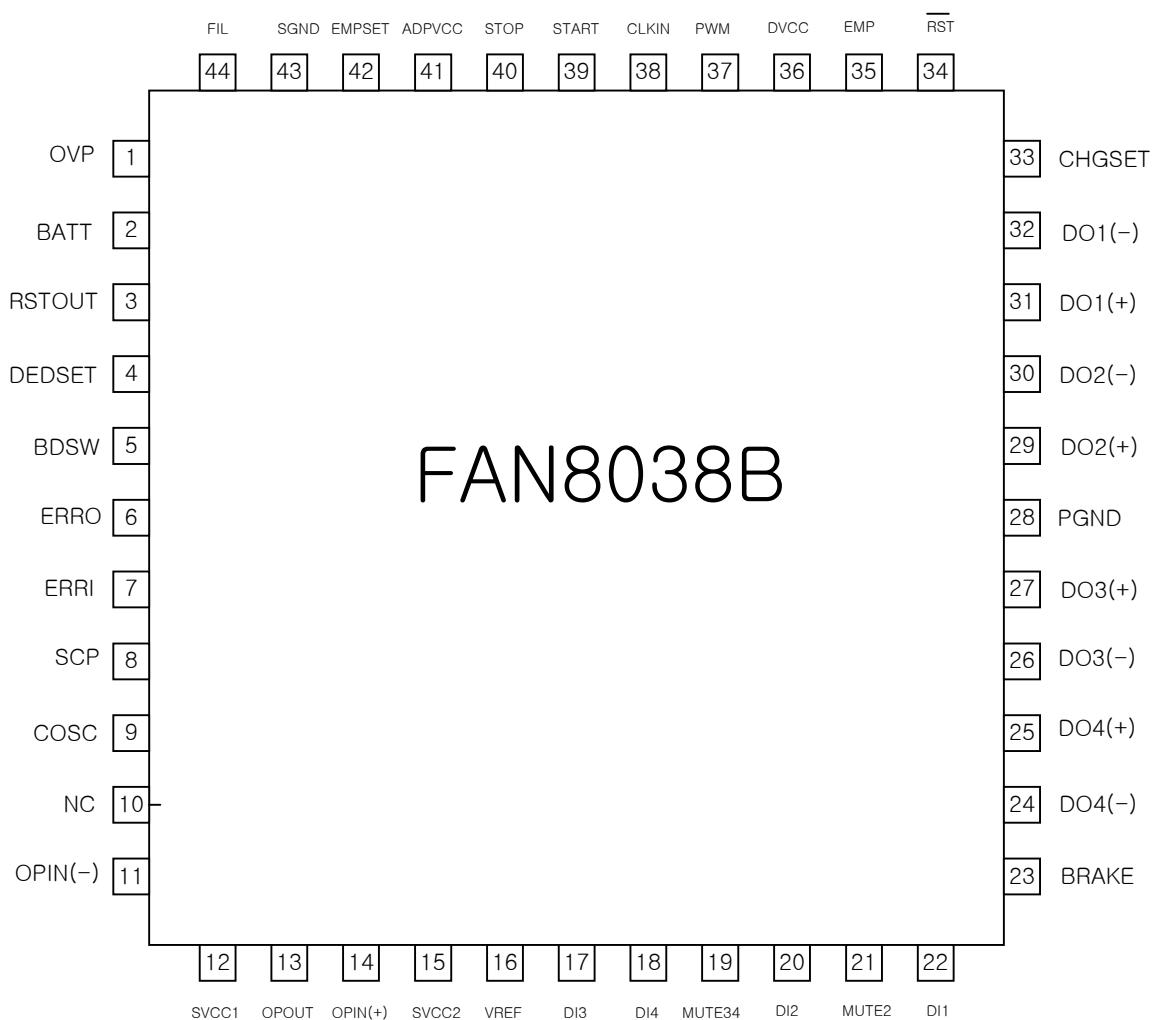
Typical application

- Portable compact disk player (CDP)
- Portable Mini disk player (MD)
- Disc-man
- Other portable compact disk media

Ordering Information

Device	Package	Operating Temp.
FAN8038B	44-QFP-1010B	-35°C ~ +85°C

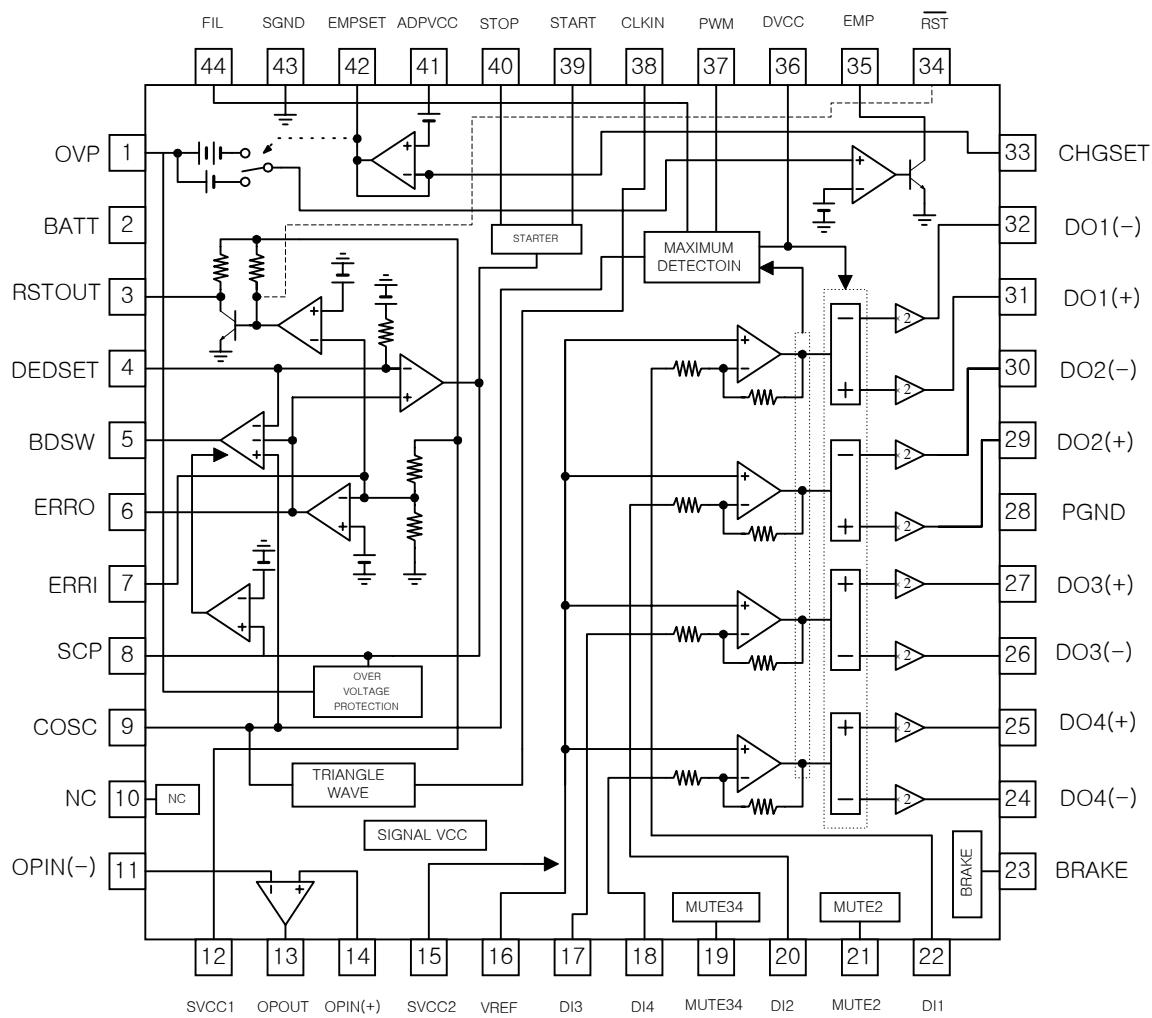
Pin Assignments



Pin Definitions

Pin Number	Pin Name	Pin Function Description
1	OVP	Battery power supply mode
2	BATT	Battery power supply
3	RSTOUT	RSTOUT detection output
4	DEDSET	DEDSET time setting
5	BDSW	Booster transistor drive
6	ERRO	Error amp output
7	ERRI	Error amp input
8	SCP	Short circuit protection setting
9	COSC	Triangular wave output
10	N.C	No connection
11	OPIN(-)	Op-amp negative input
12	SVCC1	control circuit power supply
13	OPOUT	Op-amp output
14	OPIN(+)	Op-amp positive input
15	SVCC2	Pre-drive power supply
16	VREF	Reference voltage
17	DI3	CH3 control signal input
18	DI4	CH4 control signal input
19	MUTE34	CH3, 4 mute
20	DI2	CH2 control signal input
21	MUTE2	CH2 mute
22	DI1	CH1 control signal input
23	BRAKE	CH1 Brake
24	DO4(-)	CH4 negative output
25	DO4(+)	CH4 positive output
26	DO3(-)	CH3 negative output
27	DO3(+)	CH3 positive output
28	PGND	Power unit power ground
29	DO2(+)	CH2 positive output
30	DO2(-)	CH2 negative output
31	DO1(+)	CH1 positive output
32	DO1(-)	CH1 negative output
33	CHGSET	Charge current setting
34	RST	RSTOUT inverting output
35	EMP	Empty detection output
36	DVCC	H-bridge power supply
37	PWM	PWM transistor drive
38	CLKIN	External clock input
39	START	Boost DC/DC converter starting
40	STOP	Boost DC/DC converter off
41	ADPVCC	Charging circuit power supply
42	EMPSET	Empty dection level converting
43	SGND	Signal ground
44	FIL	PWM phase compensation

Internal Block Diagram



Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Value	Unit
Maximum supply voltage	VCC	13.2	V
Maximum output current	IO	500	mA
Power dissipation	PD	1.0	W
Operating temperature	TOPR	-35 ~ +85	°C
Storage temperature	TSTG	-55 ~ +150	°C

Recommended Operating Conditions (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Charging circuit power supply voltage	ADPVCC	3.0	4.5	8.0	V
Power Supply Voltage	BATT	1.5	2.4	8.0	V
Control Circuit Power Supply voltage	SVCC	2.7	3.2	5.5	V
PRE-DRIVER Vcc	SVCC2	2.7	3.2	5.5	V
Output Voltage	VM	-	PWM	BATT	V
Operating Temperature	Ta	-10	25	70	°C

Electrical characteristics

(Ta=25°C, BATT=2.4V, SVCC1=SVCC2=3.2V, VREF=1.6V, ADPVCC=0V, fCLKIN=88.2KHz)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
COMMON SECTION						
BATT stand-by current	I _{ST}	BATT=10.5V, SVCC1,2=VREF=0V	-	-	5	µA
BATT supply current (No load)	I _{BATT}	DVCC=0.45V, MUTE34=3.2V	-	2.5	3.5	mA
SVCC supply current (NO load)	I _{SVCC1}	DVCC=0.45V, MUTE34=3.2V, ERRI=0V	-	3.0	3.5	mA
SVCC2 supply current (No load)	I _{SVCC2}	DVCC=0.45V, MUTE34=3.2V	-	3.5	5.0	mA
ADPVCC supply current (No load)	I _{ADPVCC}	ADPVCC=4.5V, ROUT=OPEN	-	0.2	1.0	mA
H-DRIVE PART						
Voltage gain CH1, 3, 4 CH2	G _{VC134} G _{VC2}	-	12 21.5	14 23.5	16 24.5	dB
Gain error by polarity	ΔG _{VC}	-	-2	0	2	dB
InputpinresistanceCH1,3,4 CH2	R _{DI134} R _{DI2}	IN=1.7 & 1.8V	9 6	11 7.5	13 9	KΩ
Maximum output voltage	V _{OUT}	RL=8Ω, DVCC=BATT=4V, IN=0 ~ 3.2V	1.9	2.1	-	V
Saturation voltage (Lower)	V _{SAT1}	IO=-300mA, IN=0 & 3.2V	-	240	400	mV
Saturation voltage (Upper)	V _{SAT2}	IO=300mA, IN=0 & 3.2V	-	240	400	mV
Input offset voltage	V _{IO}	-	-8	0	8	mV
OutputoffsetvoltageCH1,3,4 CH2	V _{OO134} V _{OO2}	VREF=IN=1.6V	-70 -130	0 0	70 130	mV
DEAD zone	V _{DB}	-	-30	0	30	mV
Brake1 on voltage	V _{M1ON}	DI1=1.8V	2.0	-	-	V
Brake1 off voltage	V _{M1OFF}	DI1=1.8V	-	-	0.8	V
MUTE2 on voltage	V _{M2ON}	DI2=1.8V	2.0	-	-	V
MUTE2 off voltage	V _{M2OFF}	DI2=1.8V	-	-	0.8	V
MUTE34 on voltage	V _{M34ON}	DI3=DI4=1.8V	-	-	0.8	V
MUTE34 off voltage	V _{M34OFF}	DI3=DI4=1.8V	2.0	-	-	V
VREF on voltage	V _{REFON}	INn=1.8V(N=1, 2, 3, 4)	1.2	-	-	V
VREF off voltage	V _{REFOFF}	INn=1.8V(N=1, 2, 3, 4)	-	-	0.8	V
BRAKE1 brake current	I _{BRAKE}	brake current	4	7	10	mA

Electrical Characteristics (Continued)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
PWM POWER SUPPLY DRIVING						
PWM sink current	I _{PWM}	DI1=2.1V	10	13	17	mA
DVCC level shift voltage	V _{SHIF}	DI1=1.8V, DVCC-OUT1F	0.35	0.45	0.55	V
DVCC leak current	I _{DLK}	DVCC=9V, SVCC1,2=BATT=0V	-	0	5	μA
PWM amp transfer gain	G _{PWM}	DI1=1.8V, DVCC=1.2V ~ 1.4V	1/60	1/50	1/40	1/KΩ
DC/DC CONVERTER						
ERROR AMP						
SVCC1 pin threshold voltage	V _{S1TH}	-	3.05	3.20	3.35	V
ERRO pin output voltage H	V _{EOH}	ERRI=0.7V, IO=-100μA	1.4	1.6	-	V
ERRO pin output voltage L	V _{EOL}	ERRI=1.3V, IO=100μA	-	-	0.3	V
SHORT CIRCUIT PROTECTION						
SCP pin voltage	V _{SCP}	ERRI=1.3V	-	0	0.1	V
SCP pin current 1	I _{SCP1}	ERRI=0.7V	6	10	16	μA
SCP pin current 2	I _{SCP2}	ERRI=1.3V, OFF=0V	12	20	32	μA
SCP pin current 3	I _{SCP3}	ERRI=1.3V, BATT=9.5V	12	20	32	μA
SCP pin impedance	R _{SCP}	-	175	220	265	KΩ
SCP pin threshold voltage	V _{SCPTH}	ERRI=0.7V, COSC=470PF	1.10	1.20	1.30	V
Over-voltage protection detect	V _{OVP}	OVP Voltage	9.5	10	10.5	V
TRANSISTOR DRIVING						
BDSW pin output voltage 1H	V _{SW1H}	BATT=COSC=1.5V =SVCC2=0V, 10mA	0.78	0.98	1.13	V
BDSW pin output voltage 2H	V _{SW2H}	COSC=0V, IO=-10mA, ERRI=0.7V SCP=0V	1.0	1.5	-	V
BDSW pin output voltage 2L	V _{SW2L}	CT=2V, IO=1-mA	-	0.3	0.45	V
BDSW pin oscillating reequency 1	f _{SW1}	COSC=470pF, =SVCC2=0V	65	80	95	KHz
SW pin oscillating reequency 2	f _{SW2}	COSC=470pF, CLKIN=0V	60	70	82	KHz
BDSW pin oscillating reequency 3	f _{SW3}	COSC=470pF	-	88.2	-	KHz
BDSW pin minimum pulse width	T _{SWMIN}	COSC=470pF, ERRO=0.5 → 0.7V	0.01	-	0.6	μs
Pulse duty start	D _{SW1}	COSC=470PF, SVSS1,SVCC2=0V	40	50	60	%
MAX. pulse duty at self-running	D _{SW2}	COSC=470pF, ERRO=0.8V, CLKIN=0V	50	60	70	%
MAX. pulse duty at CLKIN synchronization	D _{SW3}	ERRO=0.8V, COSC=470pF	45	55	65	%

Electrical Characteristics (Continued)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
DEAD TIME						
DEDSET pin impedance	RDEDSET	-	52	65	78	KΩ
DEDSET pin output voltage	VDEDSET	-	0.78	0.88	0.98	V
INTERFACE						
STOP pin threshold voltage	VSTOPTH	ERRI=1.3V	2.0	-	-	V
STOP pin bias current	ISTOP	OFF=0V	75	95	115	μA
START pin on threshold voltage	VSTATH1	SVCC1,SVCC2=0V, COSC=2V	1.3	-	-	V
START pin off threshold voltage	VSTATH2	SVCC1,SVCC2=0V, COSC=2V	-	-	2.1	V
START pin bias current	ISTART	START=0V	13	16	19	μA
CLKIN pin threshold voltage H	VCLKINTH_H	-	2.0	-	-	V
CLKIN pin threshold voltage L	VCLKINTH_L	-	-	-	0.8	V
CLKIN pin bias current	ICLKIN	CLKIN=3.2V	-	-	10	μA
START CIRCUIT						
Starter switching voltage	VSSV	SVCC1,SVCC2=0V → 3.2V START=0V	2.3	2.5	2.7	V
Starter switching hysteresis width	VSSHS	START=0V	130	200	300	mV
Discharge release voltage	VDIS	-	1.63	1.83	2.03	V
RESET CIRCUIT						
SVCC1 RESET threshold voltage ratio	RRSTOTH	-	85	90	95	%
RESET detection hysteresis width	VRSTHS	-	25	50	100	mV
RSTOUT pin output voltage	VRSTO	IO=1mA, SVCC1,SVCC2=2.8V	-	-	0.5	V
RSTOUT pin pull up resistance	RRSTO	-	72	90	108	KΩ
RST pin output voltage 1	VRST1	IO=-1mA, SVCC1,SVCC2=2.8V	2.0	-	2.4	V
RST pin output voltage 2	VRST2	IO=-1mA, SVCC1,SVCC2=0V	2.0	-	2.4	V
RST pin pull up resistance	RRST	-	77	95	113	KΩ

Electrical Characteristics (Continued)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
OP-AMP						
Input bias current	I _{BIAS}	IN(+)=1.6V	-	-	300	nA
Input offset voltage	V _{OFOP}	IN(+)=1.6V	-5.5	0	5.5	mV
High level output voltage	V _{OHOP}	RL=OPEN	2.8	-	-	V
Low level output voltage	V _{OLOP}	RL=OPEN	-	-	0.2	V
Output drive current (Source)	V _{SOURCE}	50Ω GND	-	-6.5	-3.0	mA
Output drive current (Sink)	V _{SINK}	50Ω SVCC	0.4	0.7	-	mA
Open loop voltage gain	G _{VO}	V _{IN} =-75dB, F=1KHz	-	70	-	dB
Slew rate	SR	-	-	0.5	-	V/μs
BATTERY CHARGING CIRCUIT						
CHGSET pin bias voltage	V _{CHGSET}	ADPVCC=4.5V, CHGSET=1.8KΩ	0.71	0.81	0.91	V
CHGSET pin output resistance	R _{CHGSET}	ADPVCC=4.5V	0.75	0.95	1.20	KΩ
EMPSET pin leak current 1	I _{EMPSET}	ADPVCC=4.5V, CHGSET=OPEN	-	-	1.0	μA
EMPSET pin leak current 2	I _{EMPSET}	ADPVCC=0.6V, CHGSET=1.8KΩ	-	-	1.0	μA
EMPSET pin saturation voltage	V _{EMPSET}	ADPVCC=4.5V, IO=300mA, CHGSET=0Ω	-	0.45	1.0	V
EMPTY DETECTION						
EMP detection voltage 1	V _{EMPT1}	V _{EMPSET} =0V	2.1	2.2	2.3	V
EMP detection voltage 2	V _{EMPT2}	I _{EMPSET} =-2μA	1.7	1.8	1.9	V
EMP detection hysteresis voltage 1	V _{EMHS1}	V _{EMPSET} =0V	25	50	100	mV
EMP detection hysteresis voltage 2	V _{EMHS2}	I _{EMPSET} =-2μA	25	50	100	mV
EMP pin output voltage	V _{EMP}	IO=1mA, OVP=1V	-	-	0.5	V
EMP pin output leak current	I _{EMPLK}	OVP=2.4V	-	-	1.0	μA
OVP pin input resistance	R _{OVP}	V _{EMPSET} =0V	17	23	27	KΩ
OVP pin leak current	I _{OVPLK}	SVCC1=SVCC2=0V, OVP=4.5V	-	-	1.0	V
EMP_SET pin detection voltage	V _{EMPSET}	V _{EMPSET} =BATT-EMPSET, OVP=2V	1.5	-	-	V
EMP_SET pin detection current	I _{EMPSET}	EMPSET	-2	-	-	μA

Application Information

1. Mute Function

- When The BRAKE Pin is low is normal operation (high is CH1 mute on).
- When The Mute2 Pin is low is normal operation (high is CH2 mute on).
- When The Mute34 Pin is high is normal operation (low is CH3,4 mute on).

2. Vref Drop Mute (Figure 1)

- When the Voltage of the mute pin is above 1V, the mute circuit is stopped and the output circuit is.

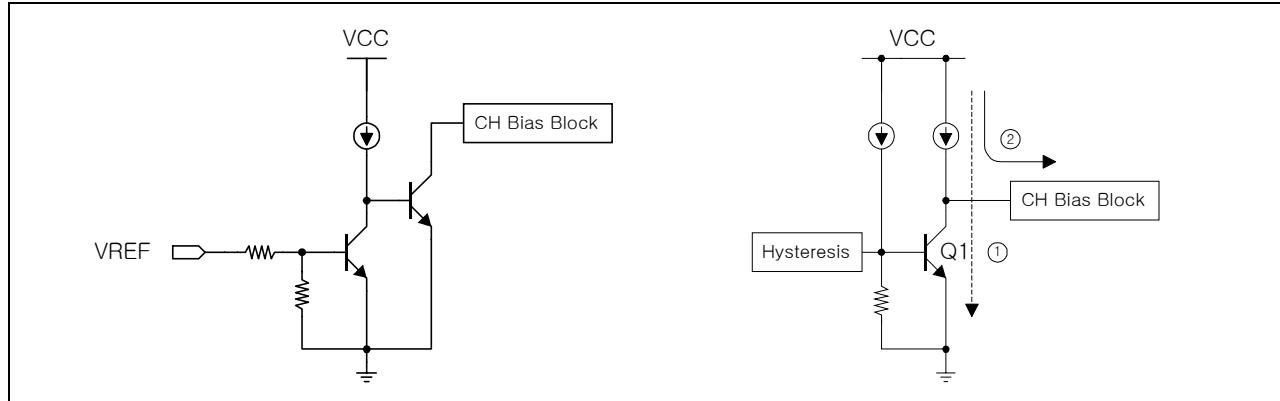


Figure 1. VREF Drop MUTE Circuit

Figure 2. TSD Circuit

3. Thermal Shutdown(Figure 2)

- If the chip temperature rises above 150°C, then the thermal shutdown (TSD) circuit is activated and the output circuit will be muted.

4. H-bridge Driver (4-Channels)

Driver input resistance is 10KΩ of CH1, CH3, CH4 and input resistance of CH2 is 7.5KΩ.

Driver gain can obtain under -mentioned

$$\text{CH1, 3, 4: } GV = 20\log \left| \frac{55K}{11K + R} \right|$$

$$\text{CH2 } GV = 20\log \left| \frac{110K}{7.5K + R} \right|$$

R is External resistance.

5. Switching Regulated Power Supply Drive

- This circuit detects a maximum output value of 4CH drivers and then generates PWM Signal.
- External Component is PNP-Tr, Coil, Schottky Diodeand Capacitor .

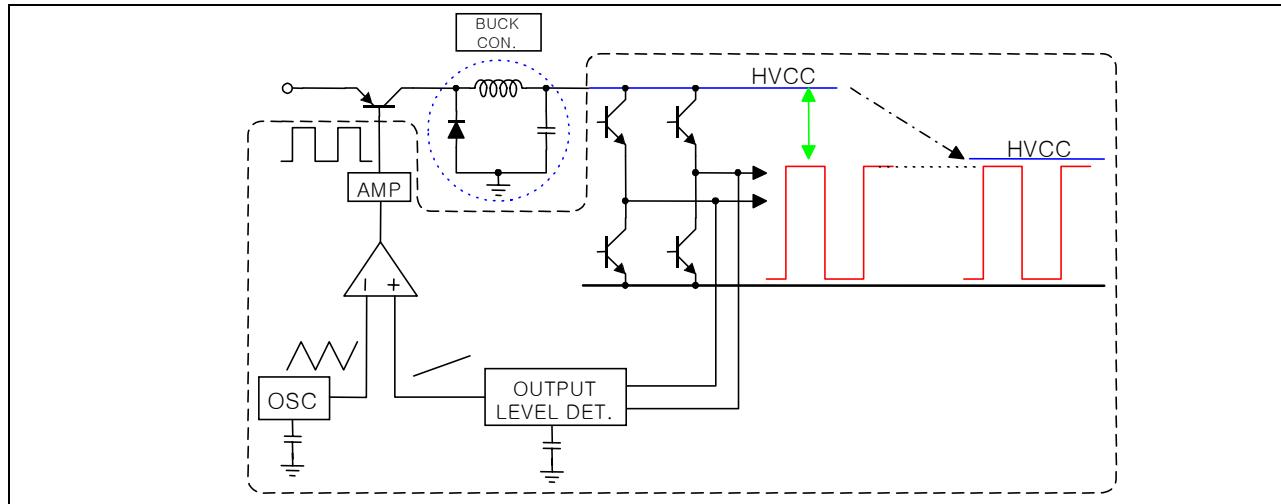


Figure 1. Switching Regulated Power Supply

6. DC/DC Converter Control Circuit

- Booster circuit needs External component. and the voltage() is defined as follows.

$$SVCC1 = 1.267 \times \frac{\frac{R1 \cdot R3}{R1 + R3} + \frac{R2 \cdot R4}{R2 + R4}}{\frac{R2 \cdot R4}{R2 + R4}}$$

R1 = Resistor1
 R2 = Resistor2
 R3 = 30KΩ
 R4 = 30.5KΩ

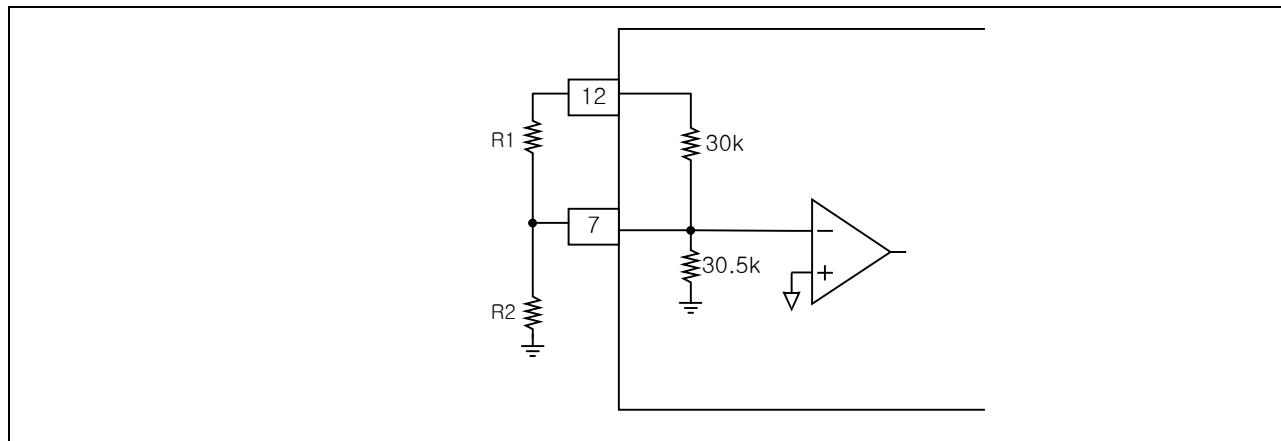


Figure 2. Output Voltage

- Short Circuit Protection function when GND and is short, ERRI become LOW and ERRO HIGH and it makes capacitor charging. fanally AMP3 is OFF.(figure 5)

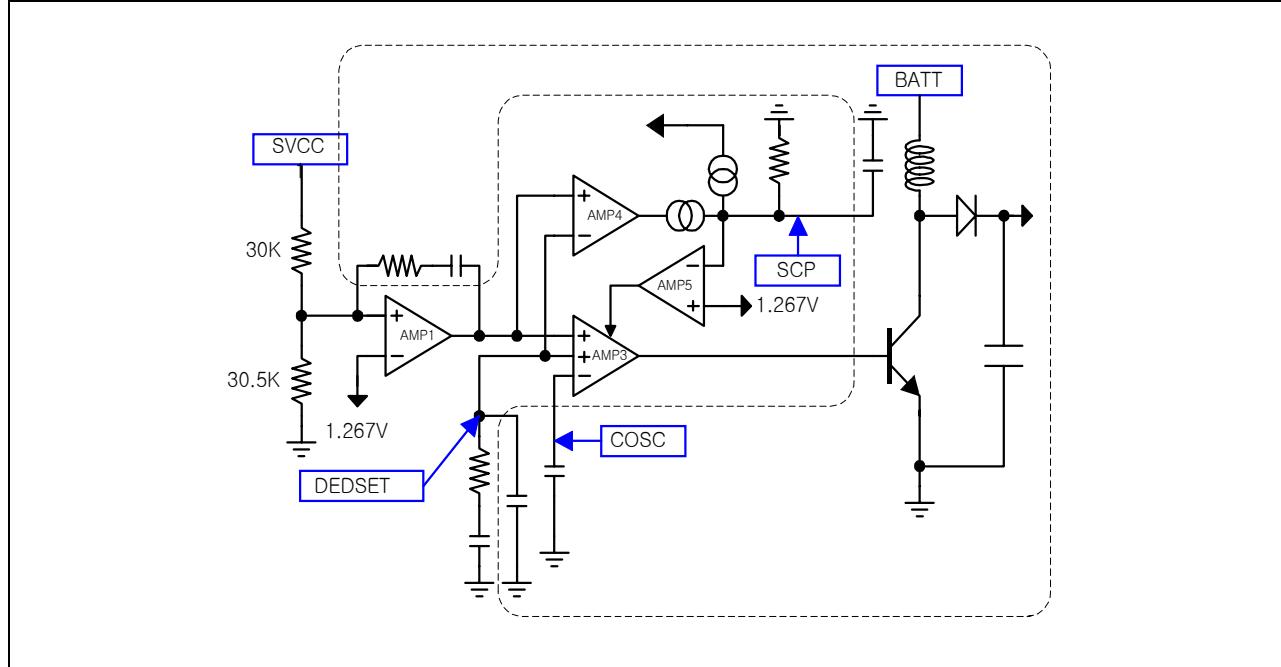


Figure 3. DC/DC Converter Control Circuit

Switching off time depen on a capacitor of the SCP . and the equation is as follow.

$$t = C_{SCP} \times \frac{V_{TH}}{I_{SCP}} \quad (V_{TH} = 1.25V, I_{SPRT} = 10\mu A)$$

- Max Duty can be controlled resistor. the equation is as follow.

$$t = C_{DEDSET} \times R \quad (R = 65K\Omega)$$

- Capacitor of the SCP terminal can control disable switiching time and it can be calculated by as follow equation.

$$t = C_{SCP} \times \frac{V_{TH}}{I_{STOP}} \quad (V_{TH} = 1.25V, I_{OFF} = 20\mu A)$$

- Over Voltage Protection BATT Voltage is over 9.7V charging SCP terminal Capacitor, it reach to VTH SW terminal signal is OFF the equation is as follow

$$t = C_{SCP} \times \frac{V_{TH}}{I_{HV}} \quad (V_{TH} = 1.25V, I_{HV} = 20\mu A)$$

- If Output Voltage of RSTOUT Circuit DC/DC Conver is over than 90%, RSTOUT terminal turn to HIGH and Hysteresis is 50mV. and RSTOUT stste is ON.

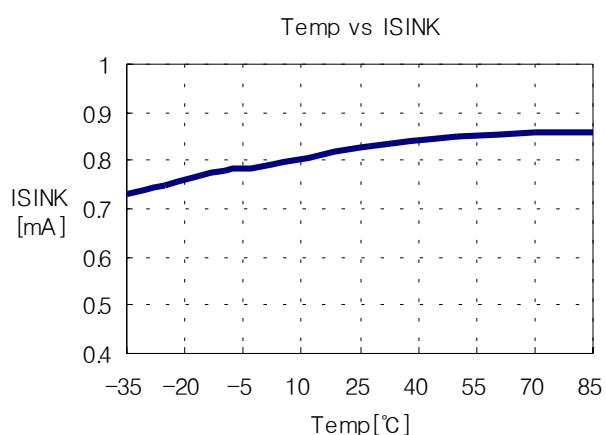
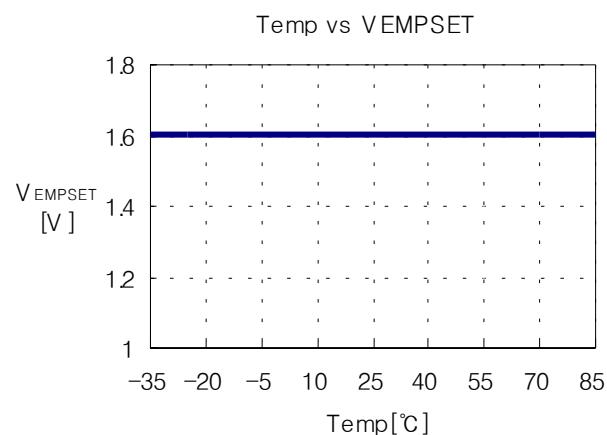
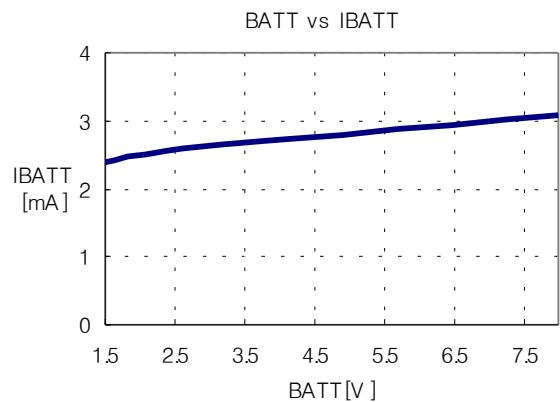
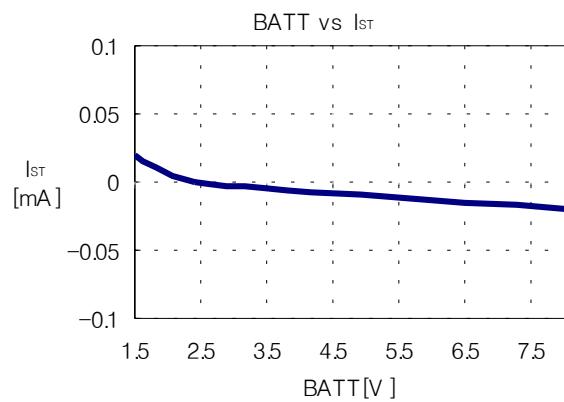
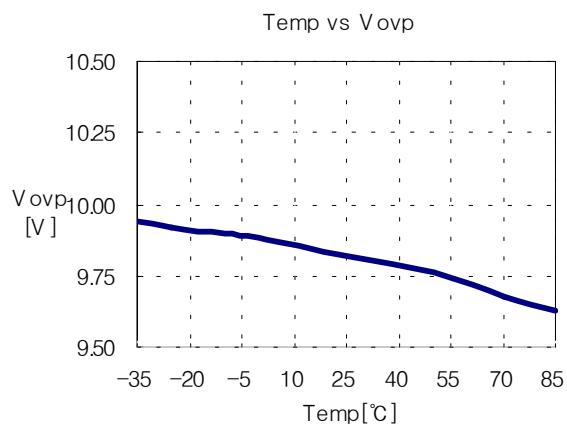
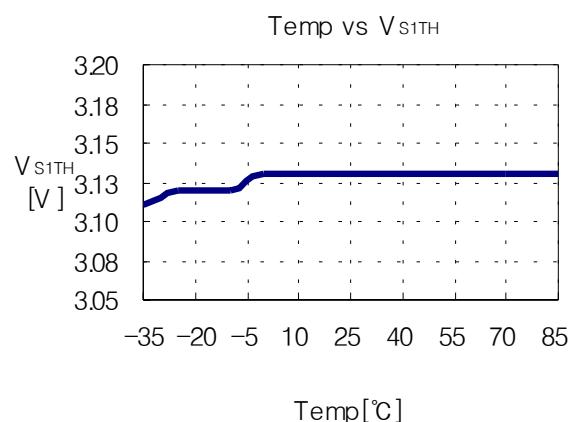
7. Empty Detecting Circuit.

EMPSET	Detect Voltage	Hysteresis	Mode
LOW	2.2V	50mV	Battery Mode
HIGH-Z	1.8V	50mV	Adapter Mode

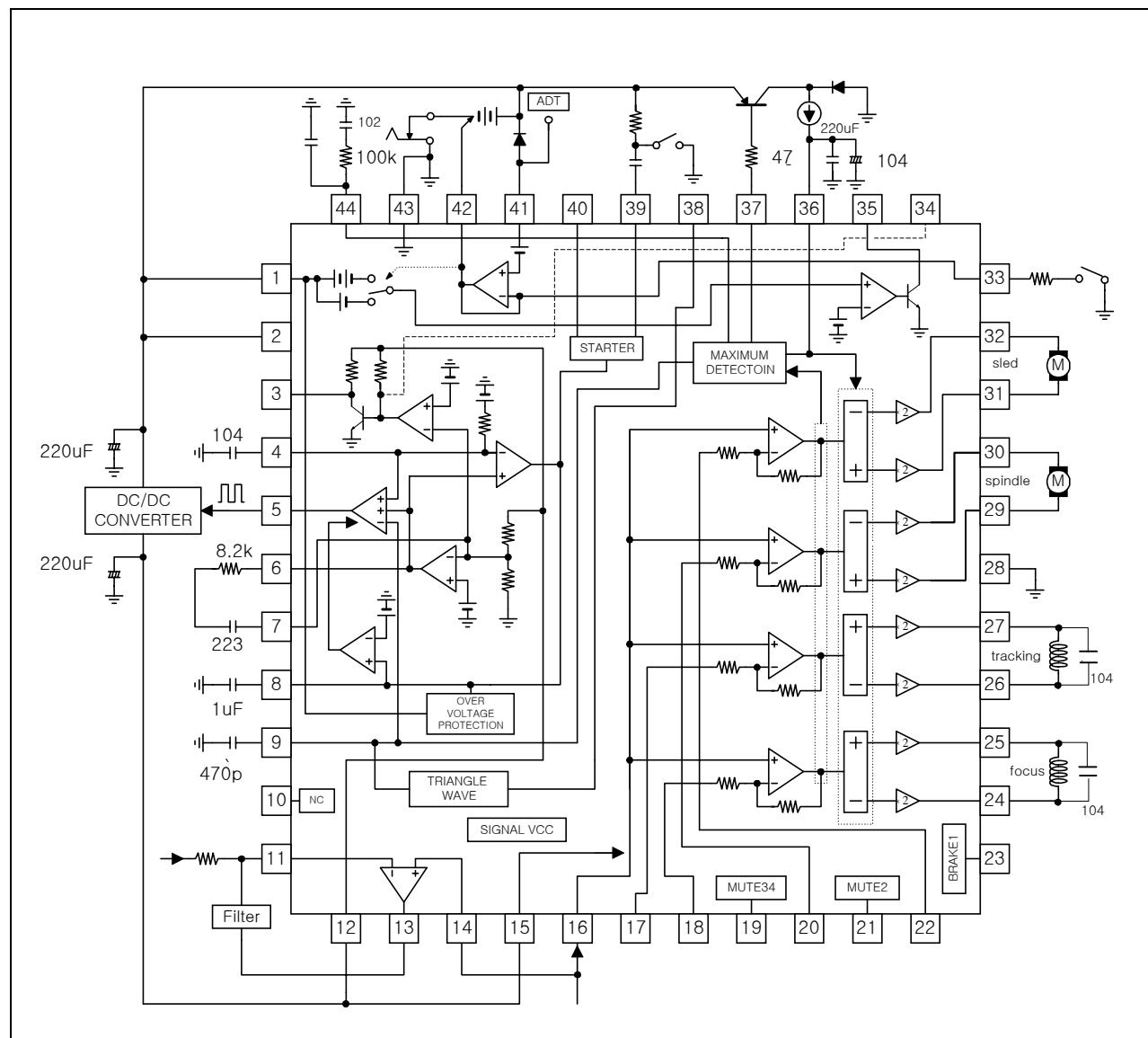
8. Battery Charging Circuit

- the battery charger circuit is separated from any other block .
- TSD operate at 150°C. Hysteresis is 30°C

Typical Performance Characteristics



Application Circuits



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